

Hilde H Hardtdegen

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205
papers

2,733
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29
h-index

40
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244
ext. papers

3,009
ext. citations

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avg, IF

4.63
L-index

#	Paper	IF	Citations
205	The Covalent Functionalization of Layered Black Phosphorus by Nucleophilic Reagents. <i>Angewandte Chemie - International Edition</i> , 2017 , 56, 9891-9896	16.4	124
204	The state of strain in single GaN nanocolumns as derived from micro-photoluminescence measurements. <i>Nano Letters</i> , 2006 , 6, 704-8	11.5	96
203	Spin-orbit coupling and phase coherence in InAs nanowires. <i>Physical Review B</i> , 2010 , 82,	3.3	74
202	The Role of Si during the Growth of GaN Micro- and Nanorods. <i>Crystal Growth and Design</i> , 2014 , 14, 1486-1492	3.5	66
201	MOVPE growth of GaAs using a N ₂ carrier. <i>Journal of Crystal Growth</i> , 1992 , 124, 420-426	1.6	60
200	Suppression of weak antilocalization in Ga _x In _{1-x} As/InP narrow quantum wires. <i>Physical Review B</i> , 2006 , 74,	3.3	59
199	Effect of Si-doping on InAs nanowire transport and morphology. <i>Journal of Applied Physics</i> , 2011 , 110, 053709	2.5	55
198	Weak antilocalization in a polarization-doped Al _x Ga _{1-x} N/GaN heterostructure with single subband occupation. <i>Applied Physics Letters</i> , 2006 , 88, 022111	3.4	49
197	Weak antilocalization in gate-controlled Al _x Ga _{1-x} N/GaN two-dimensional electron gases. <i>Physical Review B</i> , 2006 , 73,	3.3	47
196	Mechanism of mobility increase of the two-dimensional electron gas in AlGaNGaN heterostructures under small dose gamma irradiation. <i>Journal of Applied Physics</i> , 2008 , 103, 083707	2.5	43
195	Effect of carrier gas on GaN epilayer characteristics. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2006 , 3, 1408-1411		43
194	Nanoimprint and selective-area MOVPE for growth of GaAs/InAs core/shell nanowires. <i>Nanotechnology</i> , 2013 , 24, 085603	3.4	42
193	Modern chemical synthesis methods towards low-dimensional phase change structures in the Ge ₅ Sb ₇ Te ₄ material system. <i>Progress in Crystal Growth and Characterization of Materials</i> , 2015 , 61, 27-45	3.5	39
192	Demonstration of a current-controlled three-terminal Nb _{1-x} Ga _x As/InP Josephson contact. <i>Applied Physics Letters</i> , 1998 , 73, 2348-2350	3.4	39
191	Alkalimanganselenide und -telluride A ₂ Mn ₃ X ₄ Synthese, Kristall- und Spinstruktur. <i>Zeitschrift Fur Anorganische Und Allgemeine Chemie</i> , 1996 , 622, 313-318	1.3	38
190	A model structure for interfacial phase change memories: Epitaxial trigonal Ge ₁ Sb ₂ Te ₄ . <i>Journal of Alloys and Compounds</i> , 2016 , 679, 285-292	5.7	37
189	Nano-LED array fabrication suitable for future single photon lithography. <i>Nanotechnology</i> , 2015 , 26, 185302	3.4	36

188	MOVPE of n-doped GaAs and modulation doped GaAs/AlGaAs nanowires. <i>Journal of Crystal Growth</i> , 2010 , 312, 635-640	1.6	36
187	Weak antilocalization in high mobility Ga _x In _{1-x} As/InP two-dimensional electron gases with strong spin-orbit coupling. <i>Physical Review B</i> , 2007 , 76,	3.3	36
186	Direct electro-optical pumping for hybrid CdSe nanocrystal/III-nitride based nano-light-emitting diodes. <i>Applied Physics Letters</i> , 2016 , 108, 061107	3.4	36
185	Realization of nanoscaled tubular conductors by means of GaAs/InAs core/shell nanowires. <i>Nanotechnology</i> , 2013 , 24, 035203	3.4	35
184	Optimization of modulation-doped Ga _{1-x} In _x As/InP heterostructures towards extremely high mobilities. <i>Journal of Applied Physics</i> , 1993 , 73, 4489-4493	2.5	35
183	Enhanced spin-orbit scattering length in narrow Al _x Ga _{1-x} N/GaN wires. <i>Physical Review B</i> , 2007 , 76,	3.3	33
182	MOCVD of AlGaAs/GaAs with novel group III compounds. <i>Journal of Electronic Materials</i> , 1990 , 19, 305-310	1.6	33
181	Influence of growth temperature on the selective area MOVPE of InAs nanowires on GaAs (1 1 1) B using N ₂ carrier gas. <i>Journal of Crystal Growth</i> , 2009 , 311, 3813-3816	1.6	32
180	Internal strains and crystal structure of the layers in AlGaIn/GaN heterostructures grown on a sapphire substrate. <i>Journal of Applied Physics</i> , 2009 , 105, 063515	2.5	32
179	Electrical spin injection into InN semiconductor nanowires. <i>Nano Letters</i> , 2012 , 12, 4437-43	11.5	31
178	Supercurrent in Nb/InAs-nanowire/Nb Josephson junctions. <i>Journal of Applied Physics</i> , 2012 , 112, 034316.5	11.5	29
177	Electrical behaviour of the based MSM-2DEG diode. <i>Solid-State Electronics</i> , 1997 , 41, 25-31	1.7	29
176	Rashba effect in InGaAs/InP parallel quantum wires. <i>Applied Physics Letters</i> , 2006 , 88, 032102	3.4	29
175	Modeling and experimental verification of deposition behavior during AlGaAs growth: a comparison for the carrier gases N ₂ and H ₂ . <i>Journal of Crystal Growth</i> , 2001 , 223, 21-28	1.6	29
174	Manipulating InAs nanowires with submicrometer precision. <i>Review of Scientific Instruments</i> , 2011 , 82, 113705	1.7	28
173	Quantum confinement effect on the effective mass in two-dimensional electron gas of AlGaIn/GaN heterostructures. <i>Journal of Applied Physics</i> , 2009 , 105, 073703	2.5	28
172	On the magnetic properties of Gd implanted GaN. <i>Journal of Applied Physics</i> , 2008 , 103, 07D107	2.5	28
171	Characterization of interface structure in GaInAs/InP superlattices by means of X-ray diffraction. <i>Journal of Crystal Growth</i> , 1992 , 124, 583-588	1.6	28

170	In situ characterization of GaAs growth in nitrogen atmosphere during MOVPE: a comparison to hydrogen atmosphere. <i>Journal of Crystal Growth</i> , 1998 , 195, 211-216	1.6	27
169	Aharonov-Bohm effect in quasi-one-dimensional In _{0.77} Ga _{0.23} As/InP rings. <i>Physical Review B</i> , 1995 , 51, 4336-4342	3.3	27
168	Josephson effect in Nb/two-dimensional electron gas structures using a pseudomorphic In _x Ga _{1-x} As/InP heterostructure. <i>Applied Physics Letters</i> , 1997 , 71, 3575-3577	3.4	26
167	Real-time calibration of wafer temperature, growth rate and composition by optical in-situ techniques during Al _x Ga _{1-x} As growth in MOVPE. <i>Journal of Crystal Growth</i> , 2002 , 240, 87-97	1.6	26
166	Resolving ambiguities in nanowire field-effect transistor characterization. <i>Nanoscale</i> , 2015 , 7, 18188-97	7.7	25
165	Barrier height enhancement of Schottky diodes on n-In _{0.53} Ga _{0.47} As by cryogenic processing. <i>Applied Physics Letters</i> , 1993 , 63, 1939-1941	3.4	25
164	Efficient heat dissipation in AlGa _N /Ga _N heterostructure grown on silver substrate. <i>Applied Materials Today</i> , 2017 , 7, 134-137	6.6	23
163	Andreev reflection and strongly enhanced magnetoresistance oscillations in Ga _x In _{1-x} As/InP heterostructures with superconducting contacts. <i>Physical Review B</i> , 2007 , 76,	3.3	22
162	Intra-atomic photoluminescence at 1.41 eV of substitutional Mn in GaMnN of high optical quality. <i>Journal of Applied Physics</i> , 2007 , 101, 063504	2.5	22
161	Epitaxial growth and characterization of Fe thin films on wurtzite GaN(0 0 0 1). <i>Journal of Crystal Growth</i> , 2005 , 283, 500-507	1.6	22
160	Nano-light-emitting-diodes based on InGa _N mesoscopic structures for energy saving optoelectronics. <i>Applied Physics Letters</i> , 2016 , 109, 041103	3.4	21
159	Crossover from Josephson effect to single interface Andreev reflection in asymmetric superconductor/nanowire junctions. <i>Nano Letters</i> , 2014 , 14, 4977-81	11.5	19
158	Heavy carbon doping in low-pressure metalorganic vapor phase epitaxy of GaAs using trimethylarsenic: a comparison between the carrier gases N ₂ and H ₂ . <i>Journal of Crystal Growth</i> , 1994 , 145, 440-446	1.6	19
157	Novel organometallic starting materials for group III-V semiconductor metal-organic chemical vapour deposition. <i>Thin Solid Films</i> , 1989 , 174, 1-4	2.2	19
156	Magnetically and optically tunable terahertz radiation from Ta/NiFe/Pt spintronic nanolayers generated by femtosecond laser pulses. <i>Applied Physics Letters</i> , 2019 , 114, 212405	3.4	17
155	Gate-defined quantum-dot devices realized in InGaAs/InP by incorporating a HfO ₂ layer as gate dielectric. <i>Applied Physics Letters</i> , 2009 , 94, 042114	3.4	17
154	MOVPE growth and in situ characterization of GaN layers on sapphire substrates. <i>Physica Status Solidi A</i> , 2004 , 201, 312-319		17
153	Extremely high electron mobilities in modulation doped Ga _{1-x} In _x As/InP heterostructures grown by LP-MOVPE. <i>Journal of Crystal Growth</i> , 1992 , 116, 521-523	1.6	17

152	Site-controlled growth of indium nitride based nanostructures using metalorganic vapour phase epitaxy. <i>Journal of Crystal Growth</i> , 2013 , 370, 336-341	1.6	15
151	Inhomogeneity of donor doping in SrTiO ₃ substrates studied by fluorescence-lifetime imaging microscopy. <i>Applied Physics Letters</i> , 2013 , 103, 162904	3.4	15
150	MOVPE process for horizontal reactors with reduced parasitic deposition. <i>Journal of Crystal Growth</i> , 2004 , 272, 407-414	1.6	15
149	InP/InGaAs photodetector based on a high electron mobility transistor layer structure: Its response at 1.3 μ m wavelength. <i>Applied Physics Letters</i> , 1995 , 67, 106-108	3.4	15
148	Coordinatively saturated Ga compounds: A new type of group III precursor for the MOCVD of GaAs. <i>Journal of Crystal Growth</i> , 1990 , 102, 290-292	1.6	15
147	Mechanism of strain relaxation by twisted nanocolumns revealed in AlGa _x N/GaN heterostructures. <i>Applied Physics Letters</i> , 2009 , 95, 031907	3.4	14
146	Demonstration of the N ₂ carrier process for LP-MOVPE of. <i>Journal of Crystal Growth</i> , 1997 , 170, 103-108	1.6	14
145	Zeeman splitting in ballistic GaInAs/InP split-gate quantum point contacts. <i>Applied Physics Letters</i> , 2007 , 90, 122107	3.4	14
144	Direct determination of the Andreev reflection probability by means of point contact spectroscopy. <i>Applied Physics Letters</i> , 2000 , 76, 1152-1154	3.4	14
143	Fully photon operated transistor / all-optical switch based on a layered Ge ₁ Sb ₂ Te ₄ phase change medium. <i>FlatChem</i> , 2020 , 23, 100186	5.1	14
142	Long electron spin coherence in ion-implanted GaN: The role of localization. <i>Applied Physics Letters</i> , 2013 , 102, 192102	3.4	13
141	Optical and structural properties of MOVPE grown Ga _x In _{1-x} As/InP strained multiple quantum well structures. <i>Journal of Electronic Materials</i> , 1992 , 21, 293-298	1.9	13
140	Metal organic vapor phase epitaxy of hexagonal Ge ₂ Sb ₂ Te ₄ (GST). <i>Journal of Crystal Growth</i> , 2015 , 420, 37-41	1.6	12
139	Preparation of Ohmic contacts to GaAs/AlGaAs-core/shell-nanowires. <i>Applied Physics Letters</i> , 2012 , 100, 042103	3.4	12
138	Rashba effect in strained InGaAs/InP quantum wire structures. <i>Science and Technology of Advanced Materials</i> , 2003 , 4, 19-25	7.1	12
137	On the influence of gas inlet configuration with respect to homogeneity in a horizontal single wafer MOVPE reactor. <i>Journal of Crystal Growth</i> , 2001 , 223, 15-20	1.6	12
136	Magnetic properties of Gd-doped GaN. <i>Physica Status Solidi (B): Basic Research</i> , 2014 , 251, 1673-1684	1.3	11
135	Spin-orbit coupling in Ga _x In _{1-x} As/InP two-dimensional electron gases and quantum wire structures. <i>Semiconductor Science and Technology</i> , 2009 , 24, 064001	1.8	11

134	Non-uniform distribution of induced strain in a gate-recessed AlGa _N /Ga _N structure evaluated by micro-PL measurements. <i>Semiconductor Science and Technology</i> , 2012 , 27, 105008	1.8	11
133	The growth mechanism of Ga _N with different H ₂ /N ₂ carrier gas ratios. <i>Journal of Crystal Growth</i> , 2007 , 307, 6-13	1.6	11
132	A new approach towards low-pressure metalorganic vapor phase epitaxy of (AlGa)As using triethylgallium and dimethylethylaminealane. <i>Journal of Crystal Growth</i> , 1994 , 145, 478-484	1.6	11
131	Laser micro annealing conditioning for the suppression of statistical scatter in freestanding Sb ₂ Te ₃ nanowire resistance. <i>FlatChem</i> , 2020 , 21, 100164	5.1	11
130	Low-temperature conductance of the weak junction in InAs nanowire in the field of AFM scanning gate. <i>JETP Letters</i> , 2011 , 93, 10-14	1.2	10
129	Femtosecond and highly sensitive GaAs metal-semiconductor-metal photodetectors grown on aluminum mirrors/pseudo-substrates. <i>Semiconductor Science and Technology</i> , 2010 , 25, 075001	1.8	10
128	Magnetism in Ga _N layers implanted by La, Gd, Dy and Lu. <i>Thin Solid Films</i> , 2011 , 519, 6120-6125	2.2	10
127	Rashba effect in Ga _x In _{1-x} As/InP quantum wire structures. <i>Applied Physics A: Materials Science and Processing</i> , 2007 , 87, 577-584	2.6	10
126	MOVPE Ga _N growth: determination of activation energy using in-situ reflectometry. <i>Journal of Crystal Growth</i> , 2004 , 272, 100-105	1.6	10
125	Uniform III-nitride growth in single wafer horizontal MOVPE reactors. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2005 , 202, 744-748	1.6	10
124	Novel HEMT layout: The RoundHEMT. <i>Electronics Letters</i> , 1995 , 31, 589-591	1.1	10
123	(AlGa)As grown by low pressure metalorganic vapor phase epitaxy using a N ₂ carrier. <i>Journal of Electronic Materials</i> , 1994 , 23, 1061-1065	1.9	10
122	Frequency anomaly in the Rashba-effect induced magnetization oscillations of a high-mobility two-dimensional electron system. <i>Physical Review B</i> , 2013 , 87,	3.3	9
121	Spectral Sensitivity Tuning of Vertical InN Nanopyramid-Based Photodetectors. <i>Japanese Journal of Applied Physics</i> , 2013 , 52, 08JF05	1.4	9
120	Use of SiC band gap temperature dependence for absolute calibration of emissivity corrected pyrometers in III-nitride MOVPE. <i>Journal of Crystal Growth</i> , 2004 , 272, 81-86	1.6	9
119	Adjustment of the critical current in a Nb _{1-x} Ga _{1-x} As/InP Josephson contact by light exposure. <i>Applied Physics Letters</i> , 1999 , 75, 391-393	3.4	9
118	Nucleation of wavy growth modes in quantum well stacks of III-V compound alloys. <i>Journal of Crystal Growth</i> , 1995 , 152, 115-126	1.6	9
117	Evolution and characteristics of Ga _N nanowires produced via maskless reactive ion etching. <i>Nanotechnology</i> , 2014 , 25, 255301	3.4	8

116	Experimental determination of Rashba and Dresselhaus parameters and g^* -factor anisotropy via Shubnikov-de Haas oscillations. <i>New Journal of Physics</i> , 2017 , 19, 103012	2.9	8
115	g -factor and exchange energy in a few-electron lateral InGaAs quantum dot. <i>Applied Physics Letters</i> , 2009 , 95, 192112	3.4	8
114	Origin and limiting mechanism of induced nonequilibrium currents in gated two-dimensional electron systems. <i>Physical Review B</i> , 2009 , 80,	3.3	8
113	Influence of growth temperature on GaN:Cr incorporation and structural properties in MOVPE. <i>Journal of Crystal Growth</i> , 2009 , 312, 1-9	1.6	8
112	Electrical and structural studies of AlGaAs/GaAs wires grown on patterned substrates. <i>Applied Surface Science</i> , 1998 , 123-124, 687-693	6.7	8
111	On the choice of precursors for the MOVPE-growth of high-quality Al _{0.30} Ga _{0.70} As/GaAs v-groove quantum wires with large subband spacing. <i>Journal of Crystal Growth</i> , 2000 , 221, 91-97	1.6	8
110	Electron transport in modulation-doped GaAs v-groove quantum wires. <i>Physica E: Low-Dimensional Systems and Nanostructures</i> , 2000 , 7, 760-765	3	8
109	New Group III Precursors for the Movpe of GaAs and InP Based Material. <i>Materials Research Society Symposia Proceedings</i> , 1989 , 145, 205		8
108	Electrical and optical characterization of freestanding Ge ₁ Sb ₂ Te ₄ nano-membranes integrated in coplanar strip lines 2016 ,		8
107	Electronic edge-state and space-charge phenomena in long GaN nanowires and nanoribbons. <i>Nanotechnology</i> , 2017 , 28, 135204	3.4	7
106	High-field quasi-ballistic transport in AlGaIn/GaN heterostructures. <i>Applied Physics Letters</i> , 2014 , 104, 072105	3.4	7
105	Quantum dots in InAs nanowires induced by surface potential fluctuations. <i>Nanotechnology</i> , 2014 , 25, 135203	3.4	7
104	Comparison of InAs nanowire conductivity: influence of growth method and structure. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2012 , 9, 230-234		7
103	Vertically integrated (Ga, In)N nanostructures for future single photon emitters operating in the telecommunication wavelength range. <i>Nanotechnology</i> , 2013 , 24, 405302	3.4	7
102	Electron states, magneto-transport and carrier dynamics in modulation-doped V-groove quantum wires. <i>Solid-State Electronics</i> , 1998 , 42, 1245-1249	1.7	7
101	Use of wafer temperature determination for the study of unintentional parameter influences for the MOVPE of III-nitrides. <i>Physica Status Solidi (B): Basic Research</i> , 2005 , 242, 2581-2586	1.3	7
100	An outstanding innovation in LP-MOVPE: use of nitrogen as the carrier gas. <i>III-Vs Review</i> , 1995 , 8, 34-39		7
99	Suppression of wavy growth in metalorganic vapor phase epitaxy grown GaInAs/InP superlattices. <i>Applied Physics Letters</i> , 1996 , 69, 2101-2103	3.4	7

98	Compact extreme ultraviolet source for laboratory-based photoemission spectromicroscopy. <i>Applied Physics Letters</i> , 2016 , 108, 234101	3.4	7
97	Conditioning nano-LEDs in arrays by laser-micro-annealing: The key to their performance improvement. <i>Applied Physics Letters</i> , 2021 , 118, 043101	3.4	7
96	Polymorphous GdScO ₃ as high permittivity dielectric. <i>Journal of Alloys and Compounds</i> , 2015 , 651, 514-520	3.7	6
95	Investigations of local electronic transport in InAs nanowires by scanning gate microscopy at liquid helium temperatures. <i>JETP Letters</i> , 2014 , 100, 32-38	1.2	6
94	The electronic transport of top subband and disordered sea in an InAs nanowire in the presence of a mobile gate. <i>Journal of Physics Condensed Matter</i> , 2014 , 26, 165304	1.8	6
93	Self-assembled GaN nanostructures by dry etching and their optical properties. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2012 , 209, 443-446	1.6	6
92	Distortions of the coulomb blockade conductance line in scanning gate measurements of inas nanowire based quantum dots. <i>Journal of Experimental and Theoretical Physics</i> , 2013 , 116, 138-144	1	6
91	Growth of modulation-doped quantum wires on V-groove patterned substrates. <i>Journal of Crystal Growth</i> , 1997 , 170, 605-610	1.6	6
90	Deep-level states in MOVPE AlGaAs:. <i>Journal of Crystal Growth</i> , 1998 , 186, 13-20	1.6	6
89	Suppression of weak antilocalization in an Al _x Ga _{1-x} N/GaN two-dimensional electron gas by an in-plane magnetic field. <i>Physical Review B</i> , 2007 , 75,	3.3	6
88	Observation of quantized conductance in split-gate In _{0.53} Ga _{0.47} As/In _{0.77} Ga _{0.23} As/InP point contacts using Cr/Au p-InP Schottky barriers. <i>Journal of Applied Physics</i> , 1998 , 83, 2360-2362	2.5	6
87	Characterization of hydrogen passivation and carbon self-compensation of highly C-doped GaAs by means of x-ray diffraction. <i>Journal of Applied Physics</i> , 1996 , 79, 710	2.5	6
86	Nano-LED induced chemical reactions for structuring processes. <i>Nanoscale Advances</i> , 2020 , 2, 5421-5427	5.1	6
85	AlGaIn/GaN Round-HEMTs on (111) silicon substrates. <i>Electronics Letters</i> , 2001 , 37, 1364	1.1	6
84	Hexagonal GdScO ₃ : an epitaxial high- ϵ dielectric for GaN. <i>Semiconductor Science and Technology</i> , 2014 , 29, 075005	1.8	5
83	Impact of thermal annealing on nonequilibrium carrier dynamics in single-crystal, freestanding GaAs mesostructures. <i>Semiconductor Science and Technology</i> , 2014 , 29, 045022	1.8	5
82	Direct observation of standing electron waves in diffusively conducting inas nanowire. <i>JETP Letters</i> , 2012 , 96, 109-112	1.2	5
81	From conformal overgrowth to lateral growth of indium arsenide nano structures on silicon substrates by MOVPE. <i>Journal of Crystal Growth</i> , 2013 , 370, 141-145	1.6	5

80	New method of creation of a rearrangeable local Coulomb potential profile and its application for investigations of local conductivity of InAs nanowires. <i>Physica E: Low-Dimensional Systems and Nanostructures</i> , 2011 , 44, 690-695	3	5
79	LaLuO ₃ as a high- κ gate dielectric for InAs nanowire structures. <i>Semiconductor Science and Technology</i> , 2010 , 25, 085001	1.8	5
78	Study on growth and electrical performance of double-heterostructure AlGaIn/GaN/AlGaIn field-effect-transistors. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2009 , 6, S1003-S1006		5
77	Monitoring structural influences on quantum transport in InAs nanowires. <i>Applied Physics Letters</i> , 2012 , 101, 062104	3.4	5
76	Influence of the reactor inlet configuration on the AlGaIn growth efficiency. <i>Journal of Crystal Growth</i> , 2007 , 298, 413-417	1.6	5
75	Shot noise of large charge quanta in superconductor/semiconductor/superconductor junctions. <i>Physical Review B</i> , 2005 , 71,	3.3	5
74	Hybrid optoelectronics based on a nanocrystal/III-N nano-LED platform 2016 ,		5
73	Correlations of the mutual positions of the nodes of charge density waves in side-by-side placed InAs wires measured with scanning gate microscopy. <i>JETP Letters</i> , 2015 , 101, 628-632	1.2	4
72	Negative differential conductance in InAs wire based double quantum dot induced by a charged AFM tip. <i>Journal of Experimental and Theoretical Physics</i> , 2012 , 115, 1062-1067	1	4
71	Residual strain in recessed AlGaIn/GaN heterostructure field-effect transistors evaluated by micro photoluminescence measurements. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2012 , 9, 911-914		4
70	Morphology evolution and optical properties of GaN nano-pyramids grown by selective area MOVPE. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2012 , 9, 624-627		4
69	Highly Transparent Conducting Polymer Top Contacts for Future III-Nitride Based Single Photon Emitters. <i>Japanese Journal of Applied Physics</i> , 2013 , 52, 08JH10	1.4	4
68	In-situ doping and implantation of GaN layers with Mn. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2009 , 6, S646-S649		4
67	Scanning tunneling microscopy with InAs nanowire tips. <i>Applied Physics Letters</i> , 2012 , 101, 243101	3.4	4
66	Preparation of transparent Nb/two-dimensional electron gas contacts by using electron cyclotron resonance plasma cleaning. <i>Journal of Applied Physics</i> , 2000 , 88, 4440	2.5	4
65	Optical and transport studies of hot electrons in modulation-doped quantum wires. <i>Physica B: Condensed Matter</i> , 1999 , 272, 101-106	2.8	4
64	Hexagonal LaLuO ₃ as high- κ dielectric. <i>Journal of Vacuum Science and Technology B: Nanotechnology and Microelectronics</i> , 2015 , 33, 01A104	1.3	3
63	Influence of silicon doping on the SA-MOVPE of InAs nanowires. <i>Materials Research Society Symposia Proceedings</i> , 2010 , 1258, 1		3

62	Strain-enhanced electron mobility anisotropy in In _x Ga _{1-x} As/InP two-dimensional electron gases. <i>Physica E: Low-Dimensional Systems and Nanostructures</i> , 2010 , 42, 1130-1133	3	3
61	Experimental realization of a two-dimensional to two-dimensional tunnel transistor. <i>Semiconductor Science and Technology</i> , 1996 , 11, 772-775	1.8	3
60	MOMBE and characterization of InAs and (Al,Ga)Sb. <i>Journal of Crystal Growth</i> , 1998 , 188, 32-38	1.6	3
59	Contributions to understanding the optical properties of partially ordered (Al _{0.3} Ga _{0.7}) _{0.52} In _{0.48} P. <i>Journal of Crystal Growth</i> , 1998 , 195, 124-131	1.6	3
58	Optoelectronic d.c. and r.f. behavior of InP/InGaAs based HEMTs. <i>Solid-State Electronics</i> , 1998 , 42, 197-200	7	3
57	The growth of Cr-doped GaN by MOVPE towards spintronic applications. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2007 , 204, 72-77	1.6	3
56	Observation of growth during the MOVPE of III-nitrides. <i>European Physical Journal Special Topics</i> , 2006 , 132, 177-183		3
55	AlGaIn/GaN HEMT Optimization Using the RoundHEMT Technology. <i>Physica Status Solidi A</i> , 2001 , 188, 199-202		3
54	A new method for controlled carbon doping in LP-MOVPE of GaAs using TMAs and mixtures of. <i>Journal of Crystal Growth</i> , 1995 , 156, 333-336	1.6	3
53	Dispersion relation, electron and hole effective masses in In _x Ga _{1-x} As single quantum wells. <i>Journal of Applied Physics</i> , 1996 , 79, 1481-1485	2.5	3
52	Electric Current and Noise in Long GaN Nanowires in the Space-Charge Limited Transport Regime. <i>Fluctuation and Noise Letters</i> , 2017 , 16, 1750010	1.2	2
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